

	U)	Document 10 US 20050127392 A1	Issue Date 20050616	Pages 20	Title Ultra high-speed SVSGe modulation-doped field effect transistors on ultra thin SOI/SGOI substrate.	Current OR 257/103	Current XRef
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1	- г	US 20050077510 A1	20050414	21	Structure for and method of fabilizing a high-mobility field-effect transistor	257/19	257/190; 257/192;
1	- г	US 20050045905 A1	20050303	.24	ULTRA HIGH SPEED SI/SIGE MODULATION-DOPED FIELD EFFECT TRANSISTORS ON ULTRA THIN	257/103	43RJ385
1	- г	US 20040219726 A1	20041104	25	SOLISSICIL SHASTBATE Methods of fabricating contact regions for FET incorporating Side	438/197	257/E21 129; 257/E21 445;
1	- г	US 20040161947 A1	20040819	25	Relaxed Side platform for high speed CMOS electronics and high speed analog circuits	438/778	257/E21 129; 257/E21 129; 257/E21 445;
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1	- : r	US 20030077867 A1	20030424	26	SPEED ANALOG CIRCUITS Rebried silicon germanium platform for high speed CMOS electronics and high speed analog circuits	438/285	257/E21.129; 257/E21.129; 257/E21.445;
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